

N-channel 900 V, 0.72 Ω typ., 7 A MDmesh™ K5

Power MOSFET in a DPAK package

Datasheet - production data

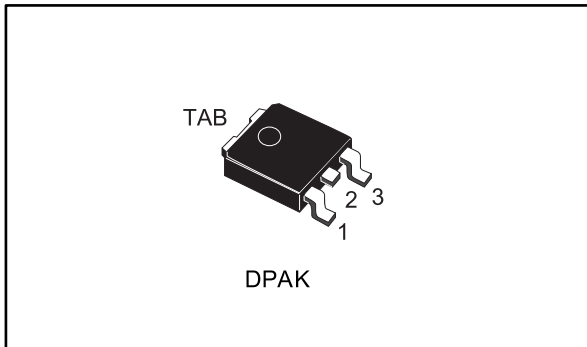
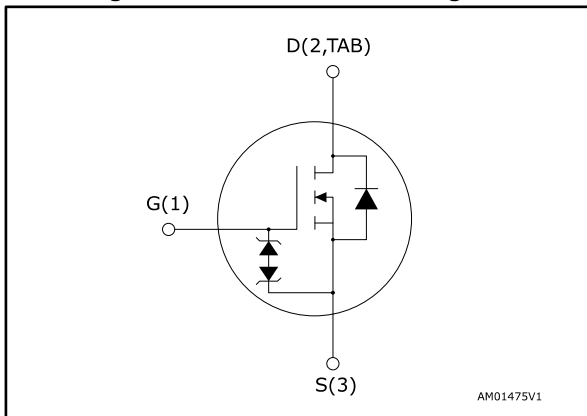


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STD7N90K5	900 V	0.81 Ω	7 A

- Industry's lowest R_{DS(on)} x area
- Industry's best FoM (figure of merit)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1: Device summary

Order code	Marking	Package	Packing
STD7N90K5	7N90K5	DPAK	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	7	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	4.4	A
$I_D^{(1)}$	Drain current (pulsed)	28	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	90	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	
T_j	Operating junction temperature range	- 55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature range		

Notes:

(1)Pulse width limited by safe operating area

(2) $I_{SD} \leq 7\text{ A}$, $di/dt \leq 100\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD} = 450\text{ V}$

(3) $V_{DS} \leq 720\text{ V}$

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.38	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient	50	$^\circ\text{C}/\text{W}$

Notes:

(1)When mounted on 1 inch² FR-4 board, 2 oz Cu.

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	2.4	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	230	mJ

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 5: On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	900			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 900\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 900\text{ V}$ $T_C = 125\text{ °C}^{(1)}$			50	μA
I_{GSS}	Gate body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DD} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 3.5\text{ A}$		0.72	0.81	Ω

Notes:

⁽¹⁾Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	425	-	pF
C_{oss}	Output capacitance		-	41	-	pF
C_{rss}	Reverse transfer capacitance		-	1.2	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0$, $V_{DS} = 0\text{ to }720\text{ V}$	-	64	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related				24	
R_g	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	6.7	-	Ω
Q_g	Total gate charge	$V_{DD} = 720\text{ V}$, $I_D = 7\text{ A}$	-	17.7	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{ V}$	-	3.1	-	nC
Q_{gd}	Gate-drain charge	(see Figure 15: "Test circuit for gate charge behavior")	-	13	-	nC

Notes:

⁽¹⁾ $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁽²⁾ $C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 450\text{ V}$, $I_D = 3.5\text{ A}$, $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see <i>Figure 14: "Test circuit for resistive load switching times"</i> and <i>Figure 19: "Switching time waveform"</i>)	-	13.2	-	ns
t_r	Rise time		-	14.2	-	ns
$t_{d(off)}$	Turn-off delay time		-	31.6	-	ns
t_f	Fall time		-	14.7	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		7	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		28	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 7\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see <i>Figure 16: "Test circuit for inductive load switching and diode recovery times"</i>)	-	352		ns
Q_{rr}	Reverse recovery charge		-	3.63		μC
I_{RRM}	Reverse recovery current		-	20.6		A
t_{rr}	Reverse recovery time	$I_{SD} = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see <i>Figure 16: "Test circuit for inductive load switching and diode recovery times"</i>)	-	525		ns
Q_{rr}	Reverse recovery charge		-	4.94		μC
I_{RRM}	Reverse recovery current		-	18.8		A

Notes:

(1)Pulse width limited by safe operating area

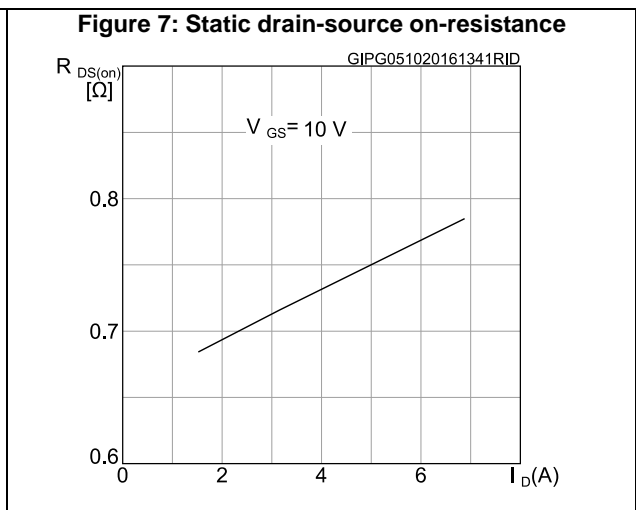
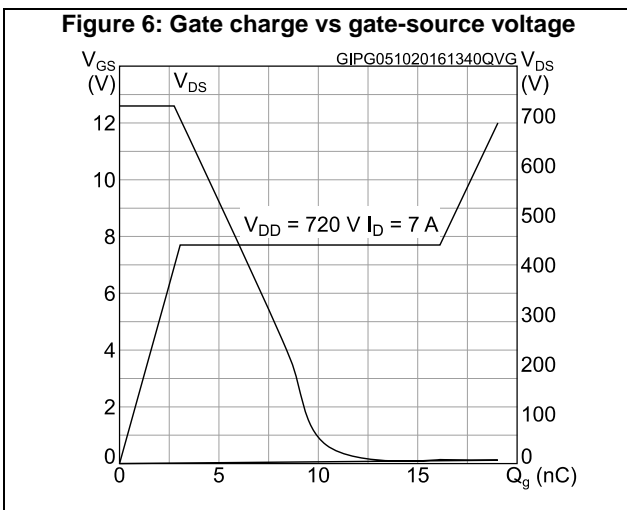
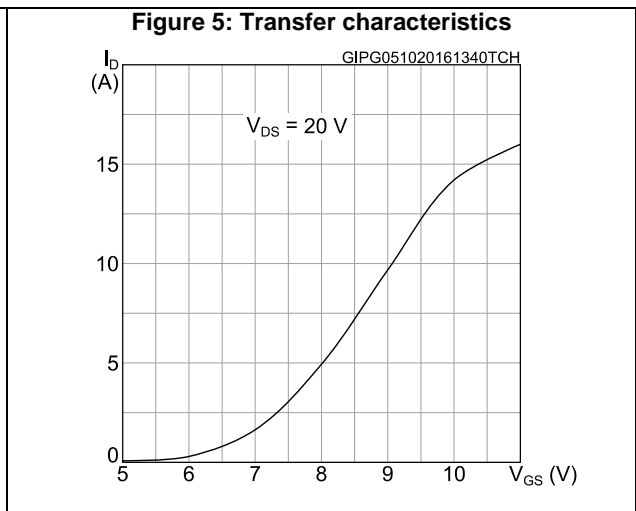
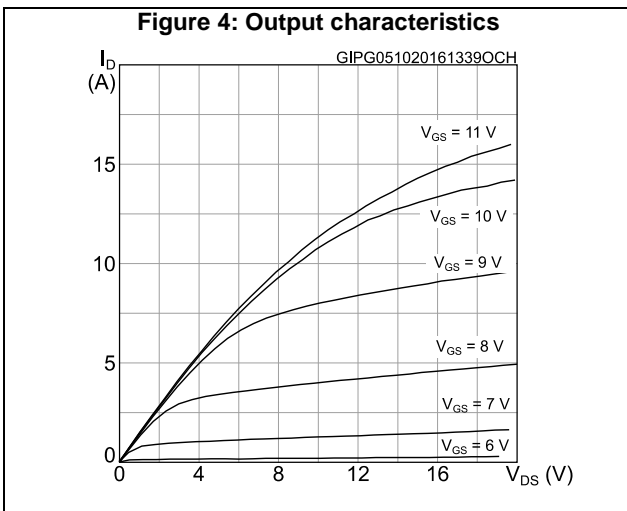
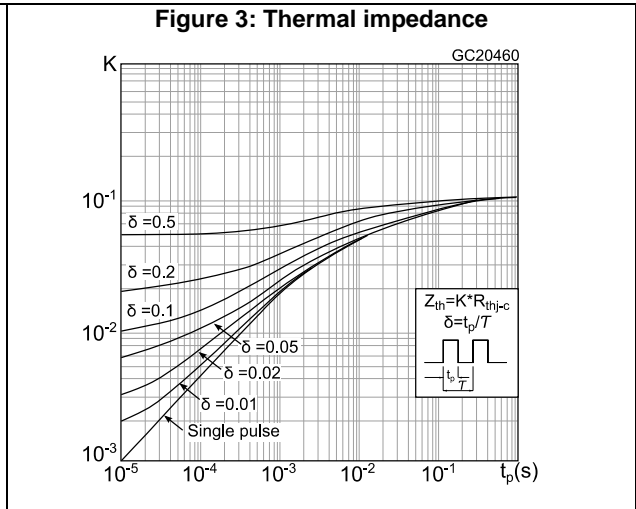
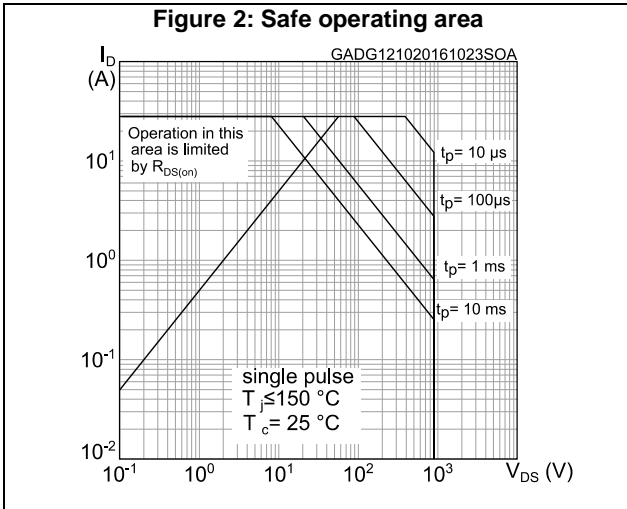
(2)Pulsed: pulse duration = 300 μs , duty cycle 1.5%

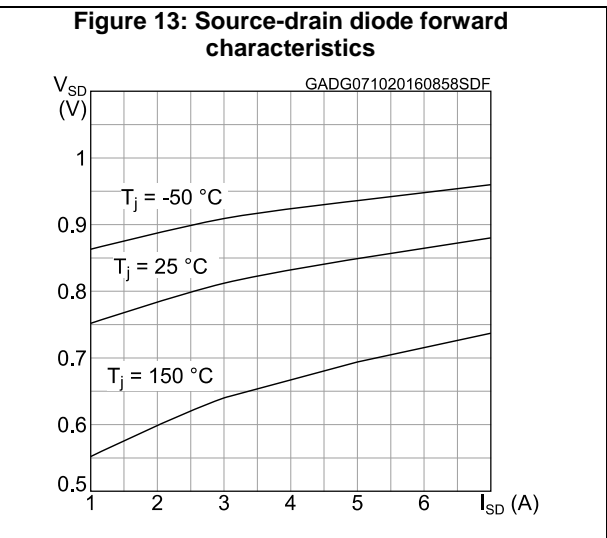
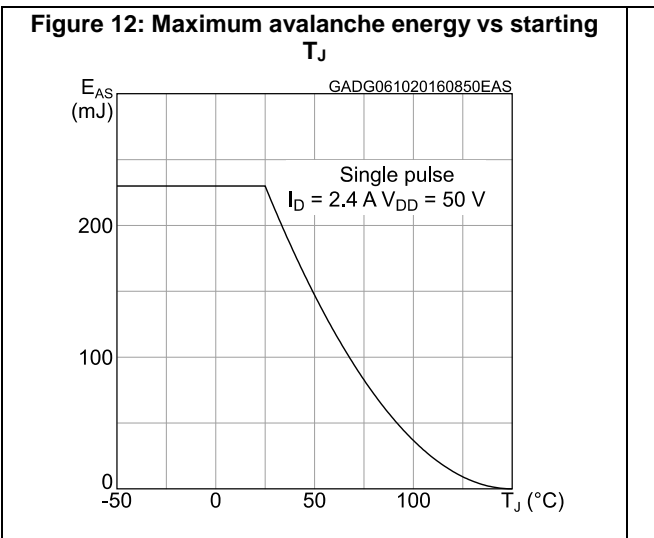
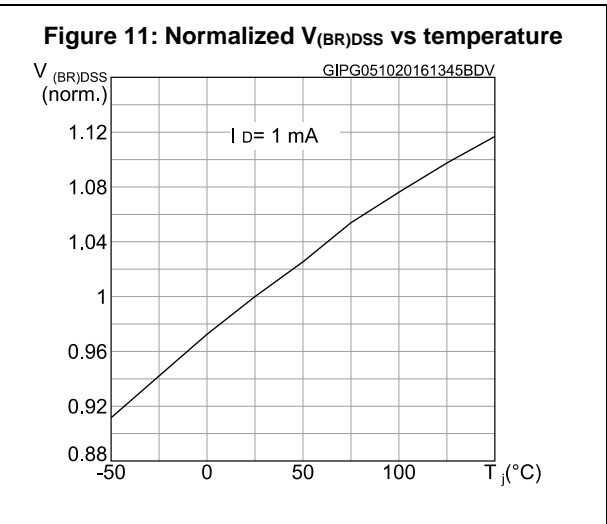
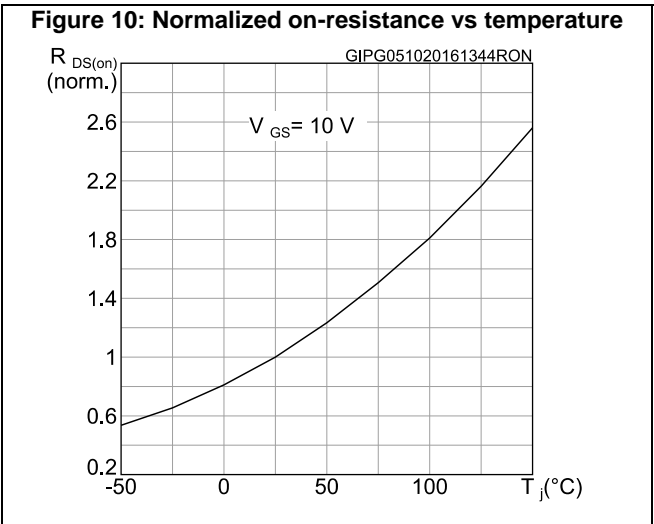
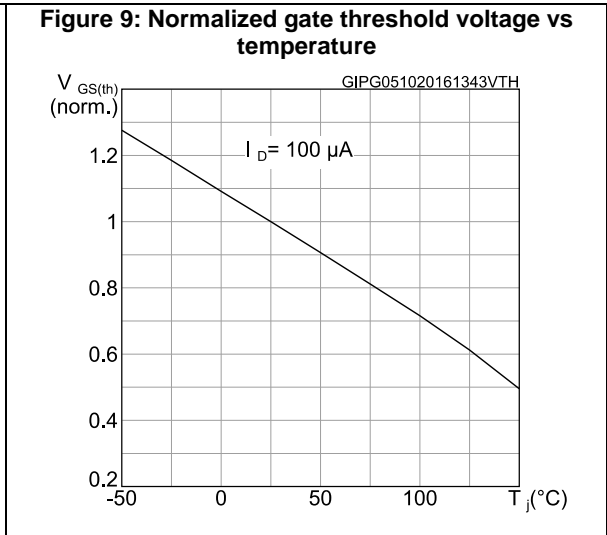
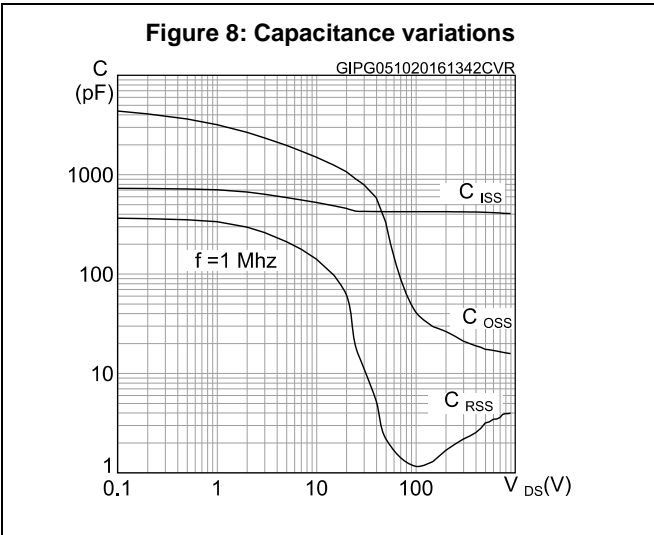
Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$, $I_D = 0\text{ A}$	± 30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

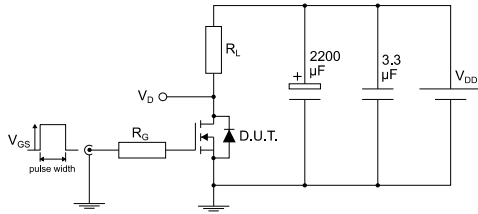
2.1 Electrical characteristics (curves)





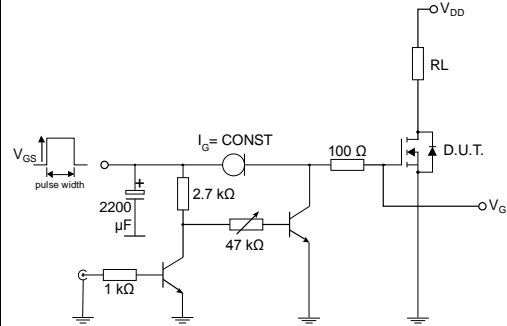
3 Test circuits

Figure 14: Test circuit for resistive load switching times



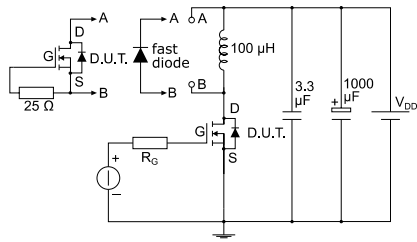
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Figure 15: Test circuit for gate charge behavior



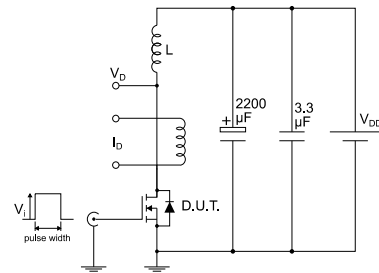
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Figure 16: Test circuit for inductive load switching and diode recovery times



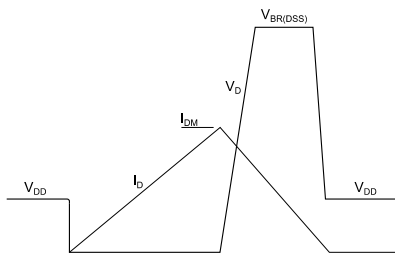
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Figure 17: Unclamped inductive load test circuit



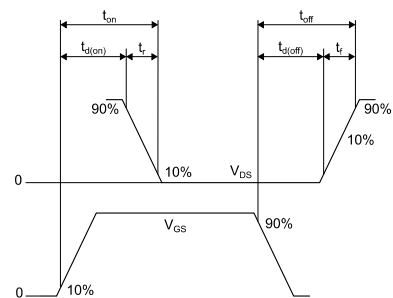
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Figure 18: Unclamped inductive waveform



AM01472v1

Figure 19: Switching time waveform



AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 DPAK type A2 package information

Figure 20: DPAK (TO-252) type A2 package outline

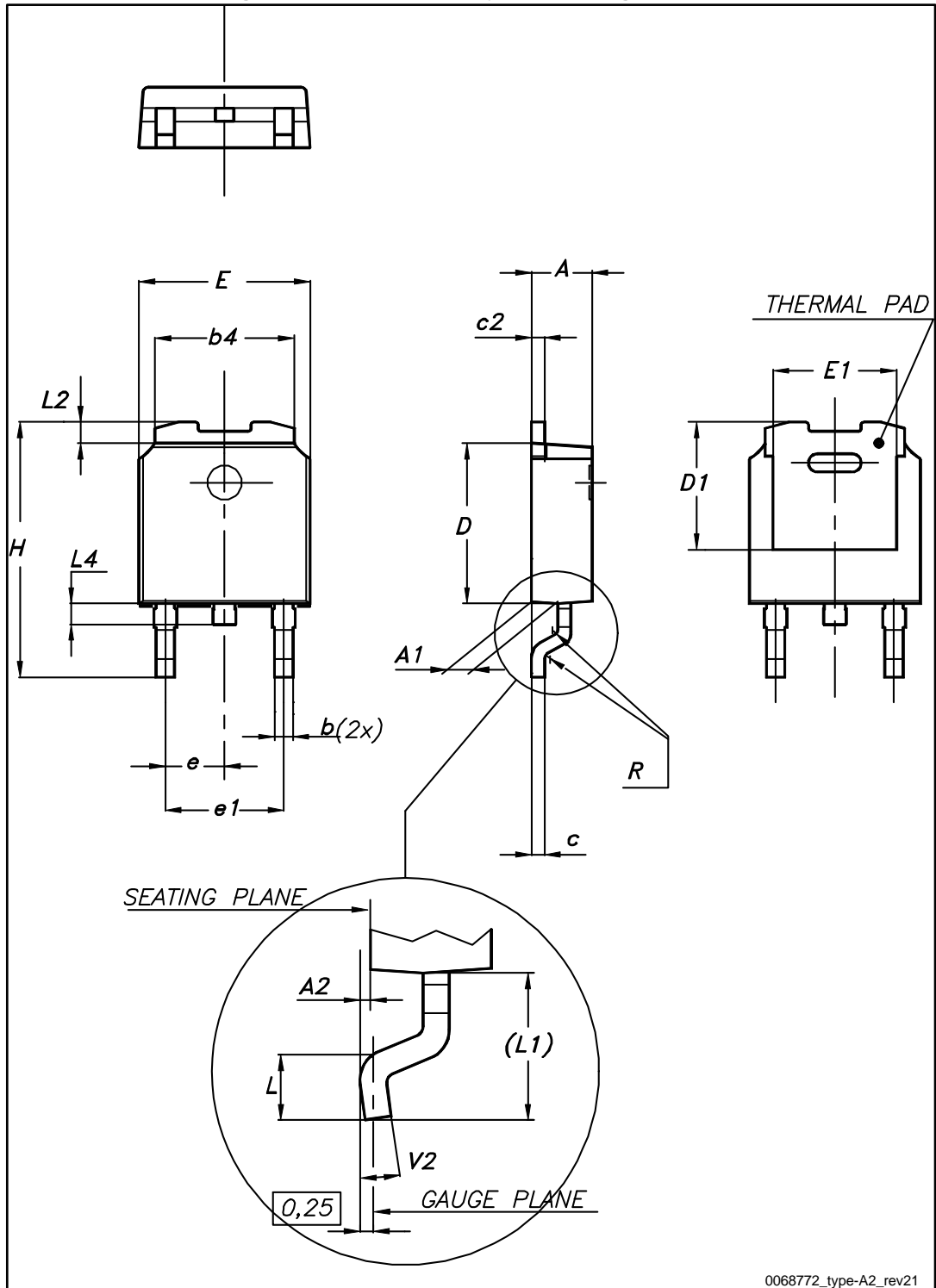
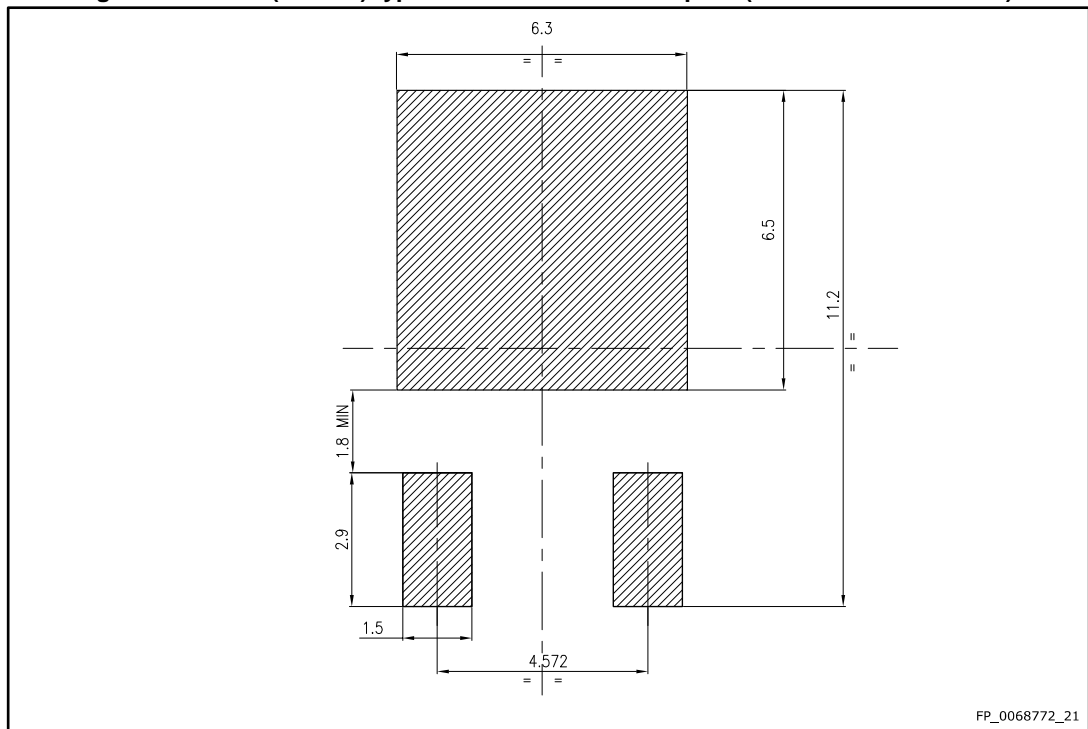


Table 10: DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 21: DPAK (TO-252) type A2 recommended footprint (dimensions are in mm)



4.2 DPAK (TO-252) packing information

Figure 22: DPAK (TO-252) tape outline

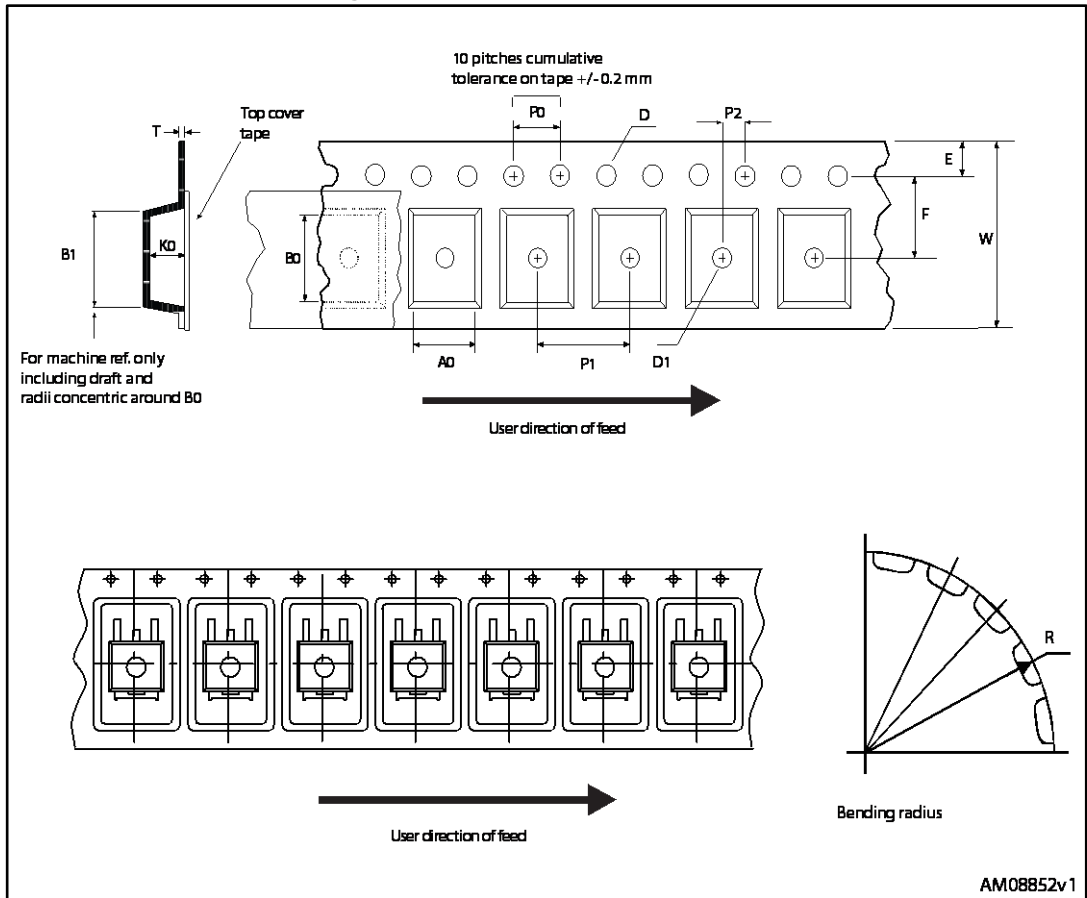


Figure 23: DPAK (TO-252) reel outline

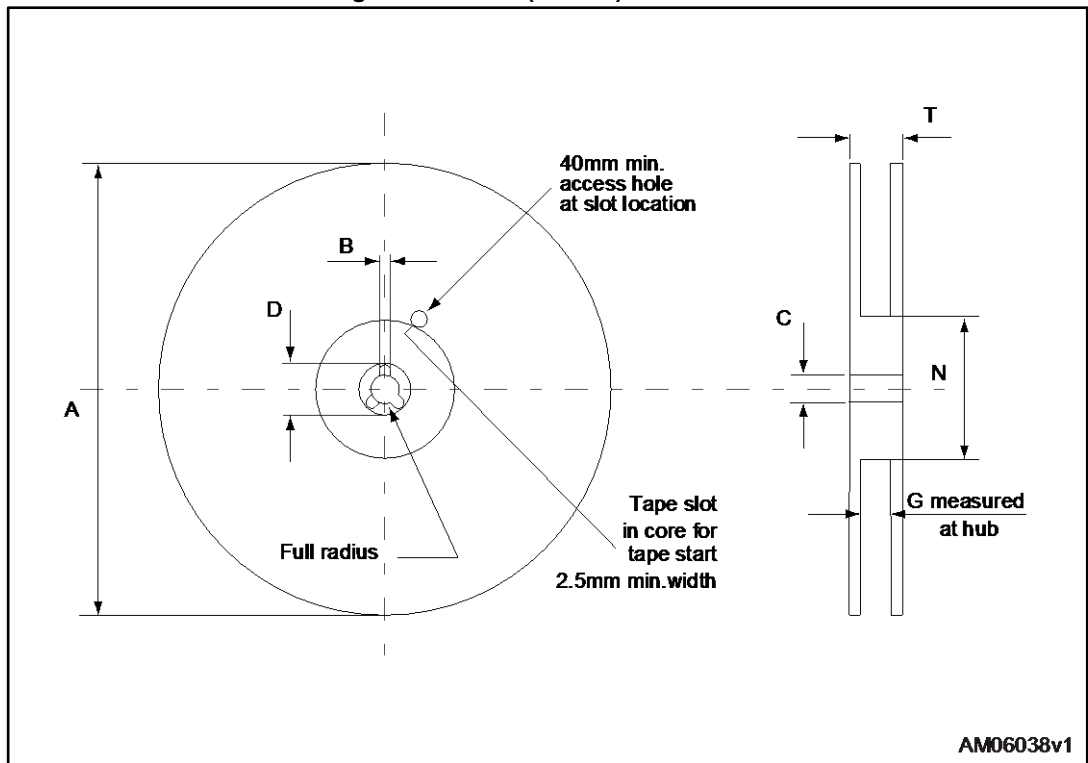


Table 11: DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

5 Revision history

Table 12: Document revision history

Date	Revision	Changes
17-Oct-2016	1	First release.

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